

MOSFETs Silicon N-Channel MOS (U-MOSIII)

# SSM3K77CT

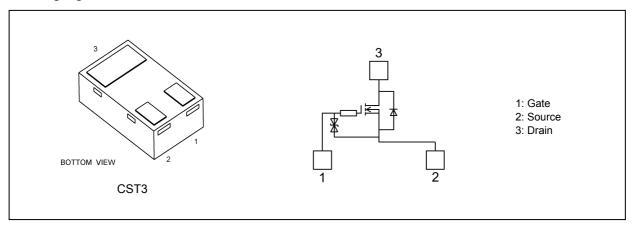
#### 1. Applications

- · High-Speed Switching
- · Analog Switches

#### 2. Features

- (1) 1.5 V gate drive voltage.
- (2) Low drain-source on-resistance
  - $\cdot$  R<sub>DS(ON)</sub> = 5.60  $\Omega$  (max) (@V<sub>GS</sub> = 1.5 V, I<sub>D</sub> = 10 mA)
  - $\cdot$  R<sub>DS(ON)</sub> = 4.05  $\Omega$  (max) (@V<sub>GS</sub> = 1.8 V, I<sub>D</sub> = 20 mA)
  - $\cdot$  R<sub>DS(ON)</sub> = 3.02  $\Omega$  (max) (@V<sub>GS</sub> = 2.5 V, I<sub>D</sub> = 50 mA)
  - $\cdot R_{\rm DS(ON)} = 2.20 \ \Omega \ ({\rm max}) \ (@V_{\rm GS} = 4.5 \ {\rm V}, \ {\rm I}_{\rm D} = 100 \ {\rm mA})$
- (3) Low leakage current

#### 3. Packaging and Internal Circuit



## 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	20	V
Gate-source voltage		V <sub>GSS</sub>	±10	
Drain current	(Note 1)	I <sub>D</sub>	200	mA
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	400	
Power dissipation	(Note 2)	P <sub>D</sub>	100	mW
Channel temperature		T <sub>ch</sub>	150	℃
Storage temperature		T <sub>stg</sub>	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Device mounted on an FR4 board. (10 mm  $\times$  10 mm  $\times$  1.0 mm ,Cu pad: 100 mm<sup>2</sup>)

Start of commercial production

2024-04



Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance,  $R_{th(ch-a)}$ , and the drain power dissipation,  $P_D$ , vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



#### 5. Electrical Characteristics

## 5.1. Static Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 5 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.08	μА
			$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V	_	_	0.08	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0 V	20	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	$I_D = 1 \text{ mA}, V_{GS} = -10 \text{ V}$	12	_	_	
Gate threshold voltage	(Note 2)	$V_{th}$	$V_{DS} = 3 \text{ V}, I_{D} = 1 \text{ mA}$	0.35	_	1.0	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	$I_D$ = 100 mA, $V_{GS}$ = 4.5 V	_	1.65	2.20	Ω
			$I_D = 50 \text{ mA}, V_{GS} = 2.5 \text{ V}$	_	2.16	3.02	
			I <sub>D</sub> = 20 mA, V <sub>GS</sub> = 1.8 V	_	2.66	4.05	
			I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 1.5 V	_	3.07	5.60	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	V <sub>DS</sub> = 3 V, I <sub>D</sub> = 100 mA	0.14	0.28	_	S

- Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.
- Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

  Take this into consideration when using the device.

Note 3: Pulse measurement.

## 5.2. Dynamic Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$	_	12	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	4.1	_	
Output capacitance	Coss		_	5.5	_	
Switching time (turn-on time)	t <sub>on</sub>	$V_{DD}$ = 10 V, $I_{D}$ = 100 mA, $V_{GS}$ = 0 to 2.5 V, $R_{GS}$ = 50 $\Omega$		18		ns
Switching time (turn-off time)	t <sub>off</sub>	Common source, See Chapter 5.3.	_	36	_	

#### 5.3. Switching Time Test Circuit

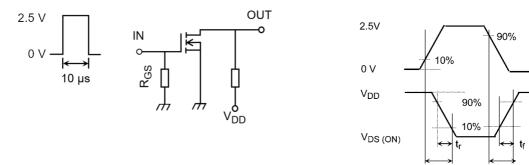


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

## 5.4. Source-Drain Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	$V_{DSF}$	$I_D = -200 \text{ mA}, V_{GS} = 0 \text{ V}$		-0.89	-1.2	V

Note 1: Pulse measurement.



## 6. Marking

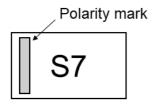


Fig. 6.1 Marking



### 7. Characteristics Curves (Note)

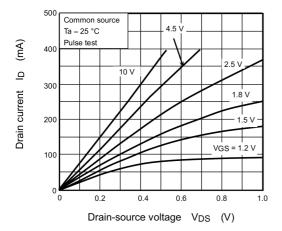


Fig. 7.1 I<sub>D</sub> - V<sub>DS</sub>

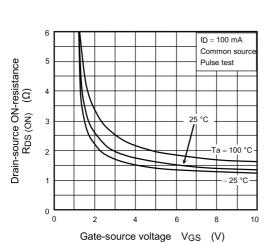


Fig. 7.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>

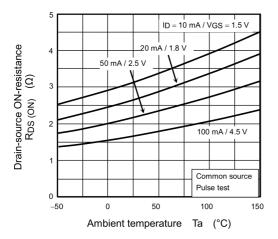


Fig. 7.5 R<sub>DS(ON)</sub> - T<sub>a</sub>

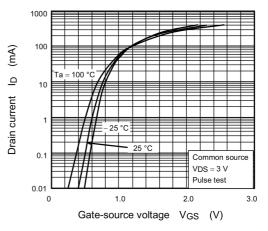


Fig. 7.2 I<sub>D</sub> - V<sub>GS</sub>

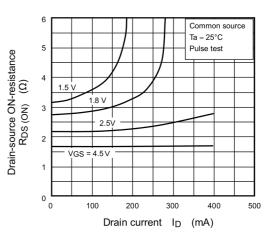


Fig. 7.4 R<sub>DS(ON)</sub> - I<sub>D</sub>

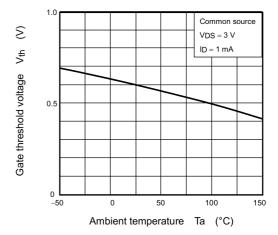


Fig. 7.6 V<sub>th</sub> - T<sub>a</sub>



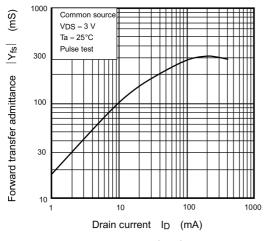


Fig. 7.7 |Y<sub>fs</sub>| - I<sub>D</sub>

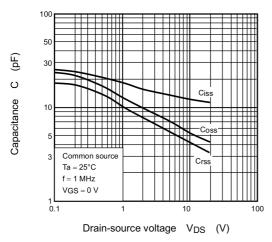


Fig. 7.9 C - V<sub>DS</sub>

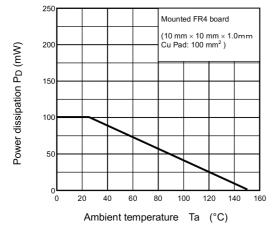


Fig. 7.11 P<sub>D</sub> - T<sub>a</sub>

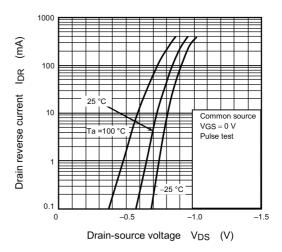


Fig. 7.8 IDR - VDS

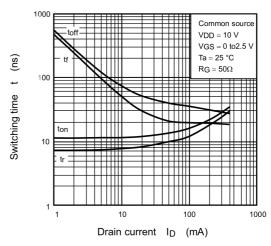


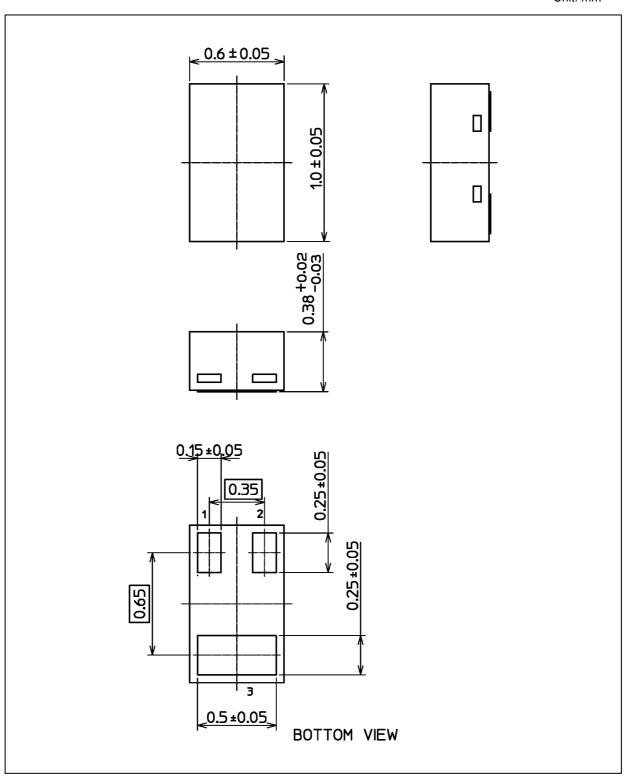
Fig. 7.10 t - I<sub>D</sub>

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 0.75 mg (typ.)

	Package Name(s)
Nickname: CST3	



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